Micralign™ Specifications

Basic Machine Performance Specifications

Resolution
1.25µm lines and spaces, UV-4 (340-440nm)
1.0µm lines and spaces, UV-3 (300-350nm)

Micralign™ shown with OS2000

Machine to Machine overlay
±0.25µm, 125/100mm systems, 98% of data
±0.30µm, 150mm systems, 98% of data

Machine to Itself overlay
±0.25µm, 98% of data

Throughput
120 wafers per hour, 125/100mm systems
100 wafers per hour, 150mm systems

Depth of Focus
± 6µm for 1.5µm lines and spaces

Focus Stability
± 2.0µm over 6 days

Focus Range
±200µm
±450µm w/ extended bellows chuck (Only available w/ OS2000)

Partial Coherence
Variable, 0.37 to 0.86

Numerical Aperture
.167

Uniformity of Illumination
±3.0%

Particulate Generation
≤ 7 particles per wafer pass (1.0µm or larger)

Prealignment and First-Level Placement Accuracy
±15µm

Footprint
18.65 sq. ft. (1.732 sq. M)

Wafer / Substrate Sizes Standard
100mm, 125mm, 150mm (other configurations available on special order)

Beta Squared Lithography, Inc.